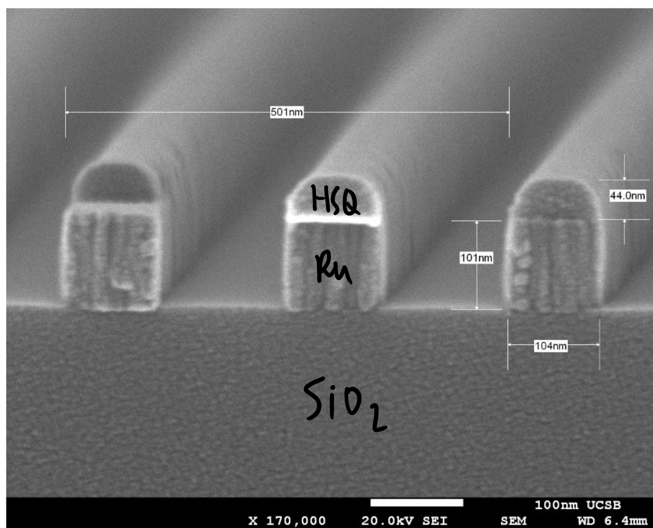
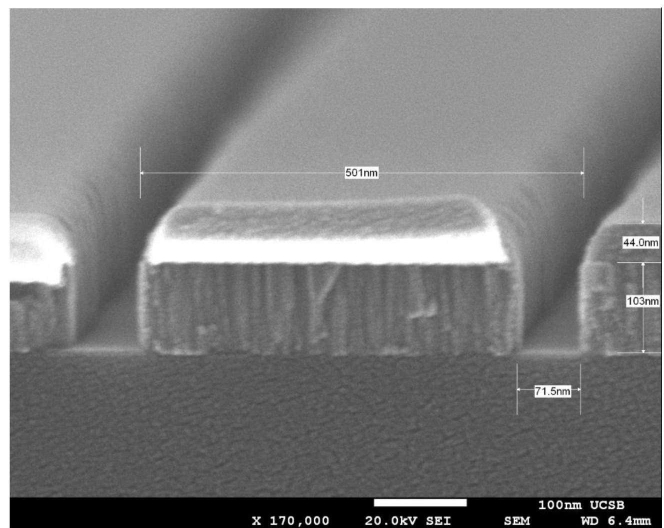
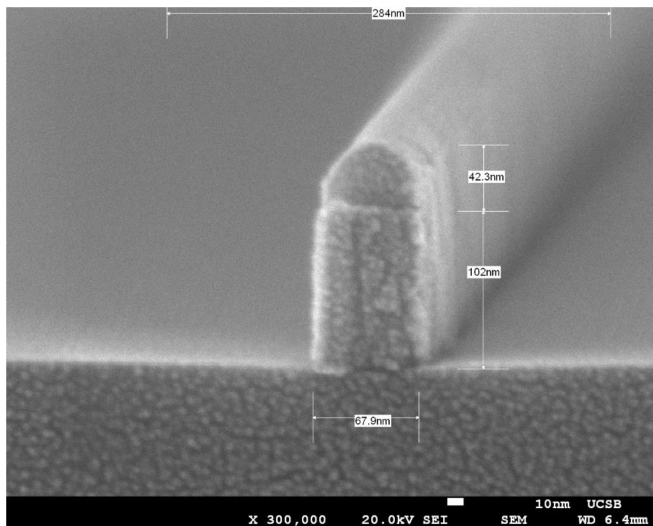
ICP2: recipe = #194 Ru Etch

(developed by Bill Mitchell, Nanofab process group)

Substrate structure		*Ru(100-110nm)/SiO2(2um)/Si*
Masking resist		*HSQ(~50nm)*
Plasma Powers	**ICP**	*500W*
	CCP[bias]	*50W*
Gas Flows	**O2**	*49.5sccm*
	Cl2	*5.5sccm*
Gas Pressures	**Ignition**	*0.5Pa*
	Etch	*2.5Pa*
Etch Data		
	Etch Rate (via laser monitor)	*Ru ~ 85nm/min, HSQ < 10nm/min*
	Etch angle	*~90 degrees (vertical!)*







Total etch time = T[end] + T[over] = 1m29ss

- T[end] = laser monitor endpoint = 1m9s
- T[over] = over etch = 20s